Supplementary Information

Cation exchange for thin film lead iodide perovskite interconversion

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Fig. S1: UV-vis spectra showing absorption of FAPbI₃ when deposited on mesoporous scaffold, with and without being heated to 170°C, compared to the black phase FAPbI₃ on a planar substrate. We observe some PbI₂ formation when heating the yellow phase on mesoporous scaffold, but not for planar devices.



Fig. S2: Full UV-Vis spectra of the interconverted films described in main text figs 1-3. a) MAPbI₃ to FAPbI₃, b) FAPbI₃ to MAPbI₃ and c) MAPbI₃ in mesoporous scaffold to FAPbI₃.





Fig. S3: X-ray diffraction spectra for the 3 interconversion reactions. a) MAPbI₃ to FAPbI₃, b) FAPbI₃ to MAPbI₃ and c) MAPbI₃ in mesoporous scaffold to FAPbI₃.



Fig. S4: Full solar cell parameter data extracted from current voltage curves measured under AM1.5 illumination, for MAPbl₃ to FAPbl₃ conversion, for at least 7 cells per point. Stabilised power measurements taken from at least 2 cells are shown on the PCE plot as red data, and are measured by holding at the maximum power point voltage as determined by the forward bias to short circuit direction fast JV scan.



Fig. S5: Full solar cell parameter data extracted from current voltage curves measured under AM1.5 illumination, for FAPbl₃ to MAPbl₃ conversion, for at least 7 cells per point. Stabilised power measurements taken from at least 2 cells per point are shown on the PCE plot as red data, and are measured by holding at the maximum power point voltage as determined by the forward bias to short circuit direction fast JV scan.



Fig. S6: Full solar cell parameter data extracted from current voltage curves measured under AM1.5 illumination, for mesostructured MAPbI₃ to FAPbI₃ conversion, for at least 7 cells per point. Stabilised power measurements taken from at least 2 cells are shown on the PCE plot as red data, and are measured by holding at the maximum power point voltage as determined by the forward bias to short circuit direction fast JV scan.